UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/563,009	12/28/2005	Toru Sawada	81844.0048	4064
²⁶⁰²¹ HOGAN & HA	7590 05/13/200 RTSON L.L.P.	EXAMINER		
1999 AVENUE OF THE STARS			BERDICHEVSKY, MIRIAM	
SUITE 1400 LOS ANGELES, CA 90067			ART UNIT	PAPER NUMBER
			4132	
			MAIL DATE	DELIVERY MODE
			05/13/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)				
	10/563,009	SAWADA ET AL.				
Office Action Summary	Examiner	Art Unit				
	MIRIAM BERDICHEVSKY	4132				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tim vill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).				
Status						
Responsive to communication(s) filed on <u>prelin</u> This action is FINAL . 2b)⊠ This Since this application is in condition for allowar closed in accordance with the practice under E	action is non-final. nce except for formal matters, pro					
Disposition of Claims						
4) ☐ Claim(s) 1-8 is/are pending in the application. 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-8 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or Application Papers 9) ☐ The specification is objected to by the Examine. 10) ☐ The drawing(s) filed on 28 December 2005 is/are Applicant may not request that any objection to the orection.	r election requirement. r. re: a)⊠ accepted or b)⊡ object drawing(s) be held in abeyance. See	e 37 CFR 1.85(a).				
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date 12/28/2005.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate				

Application/Control Number: 10/563,009 Page 2

Art Unit: 4132

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 1-4 are rejected under 35 U.S.C. 102(b) as being anticipated by Watanabe (US 4776894)

As to claim 1, Watanabe teaches a silicon based thin film solar cell, wherein a conducted type silicon based low refractive index layer (column 4, lines 36-58) and a silicon based interface layer are disposed in this order on a backside of a photoelectric conversion layer observed from a light incident side (column 4, lines 17-32).

Regarding claim 2, as there is no structural difference, the low refractive index layer with a crystalline component and a silicon based interface layer will inherently have a refractive index of not more than 2.5 at a wavelength of 600 nm.

Regarding claim 3, Watanabe teaches that the most abundantly existing constituent element, excluding silicon, in the silicon based low refractive index layer is not less than 25 atomic % (column 8, lines 36-39).

Regarding claim 4, Watanabe teaches that the most abundantly existing constituent element is oxygen (a-SiO_x) (column 4, lines 36-48).

Application/Control Number: 10/563,009 Page 3

Art Unit: 4132

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

- 4. The factual inquiries set forth in *Graham* **v.** *John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:
 - 1. Determining the scope and contents of the prior art.
 - 2. Ascertaining the differences between the prior art and the claims at issue.
 - 3. Resolving the level of ordinary skill in the pertinent art.
 - 4. Considering objective evidence present in the application indicating obviousness or nonobviousness.
- 5. Claims 5 and 7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Watanabe as applied to claim 1 above, in view of Yamagishi (US 4926230).

Applicant is directed to the paragraphs above for a complete discussion of Watanabe.

Regarding claim 5, Watanabe is silent to the silicon based low refractive index layer has a thickness of not less than 300 angstroms.

Yamagishi teaches that the silicon based low refractive index layer has a thickness of not less than 300 angstroms (column 2, lines 38-41).

Regarding claim 7, Watanabe is silent to the silicon based low refractive index layer has a thickness of not more than 150 angstroms.

Yamagishi teaches that the silicon based interface layer has a thickness not more than 150 angstroms (column 2, lines 38-41).

It would have been obvious to one of ordinary skill in the art at the time of the invention to use the thickness of the silicon based low refractive index layer of Yamagishi in Watanabe because the layer increases efficiency by promoting recombination of free electrons with electron holes, as taught by Yamagishi (column 2, lines 42-48).

6. Claims 6 and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Watanabe as applied to claims 1 (Claim 6) and to claims 1 and 7 (Claim 8) above, in view of Nakamura (JP 59035016).

Applicant is directed to the paragraphs above for a complete discussion of Watanabe.

Regarding claims 6 and 8, Watanabe is silent to the silicon based low refractive index layer comprises a crystalline silicon component in the layer.

Nakurama teaches that the silicon based low refractive index layer comprises a crystalline silicon component in the layer (abstract).

It would have been obvious to one of ordinary skill in the art at the time of the invention to use the layer with a crystalline component of Nakamura in Yagashimi because the solar cell will have the merits of both phases, as taught by Nakamura (abstract). Amorphous silicon has the advantage that it can be easily deposited over

Application/Control Number: 10/563,009 Page 5

Art Unit: 4132

large areas while the advantage of crystalline silicon is the increased stability against light exposure.

Correspondence

Any inquiry concerning this communication or earlier communications from the examiner should be directed to **MIRIAM BERDICHEVSKY** whose telephone number is (571)270-5256. The examiner can normally be reached on M-Th, 7:30am-5pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Jessica Ward can be reached on (571) 272-1223. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/M. B./ Examiner, Art Unit 4132

/Jessica L. Ward/ Supervisory Patent Examiner, Art Unit 4132 Application/Control Number: 10/563,009

Page 6

Art Unit: 4132